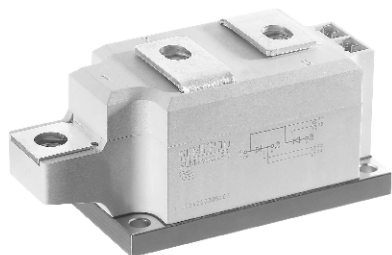


# SKKT 330, SKKH 330



**SEMIPACK® 3**

## Thyristor / Diode Modules

**SKKH 330**

**SKKT 330**

### Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

### Typical Applications\*

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instruction

| $V_{RSM}$<br>V | $V_{RRM}, V_{DRM}$<br>V | $I_{TRMS} = 510$ A (maximum value for continuous operation)<br>$I_{TAV} = 330$ A (sin. 180; $T_c = 80$ °C) |              |
|----------------|-------------------------|------------------------------------------------------------------------------------------------------------|--------------|
| 900            | 800                     | SKKT 330/08E                                                                                               | SKKH 330/08E |
| 1300           | 1200                    | SKKT 330/12E                                                                                               | SKKH 330/12E |
| 1700           | 1600                    | SKKT 330/16E                                                                                               | SKKH 330/16E |
| 1900           | 1800                    | SKKT 330/18E                                                                                               | SKKH 330/18E |

| Symbol           | Conditions                                              | Values                 | Units |
|------------------|---------------------------------------------------------|------------------------|-------|
| $I_{TAV}$        | sin. 180; $T_c = 85$ (100) °C;                          | 305 (225 )             | A     |
| $I_D$            | P16/200F; $T_a = 35$ °C; B2 / B6                        | 520 / 650              | A     |
| $I_{RMS}$        | P16/200F; $T_a = 35$ °C; W1 / W3                        | 585 / 3 * 485          | A     |
| $I_{TSM}$        | $T_{vj} = 25$ °C; 10 ms                                 | 9500                   | A     |
|                  | $T_{vj} = 130$ °C; 10 ms                                | 8000                   | A     |
| $i^2t$           | $T_{vj} = 25$ °C; 8,3 ... 10 ms                         | 451000                 | A²s   |
|                  | $T_{vj} = 130$ °C; 8,3 ... 10 ms                        | 320000                 | A²s   |
| $V_T$            | $T_{vj} = 25$ °C; $I_T = 750$ A                         | max. 1,4               | V     |
| $V_{T(TO)}$      | $T_{vj} = 130$ °C                                       | max. 0,8               | V     |
| $r_T$            | $T_{vj} = 130$ °C                                       | max. 0,6               | mΩ    |
| $I_{DD}, I_{RD}$ | $T_{vj} = 130$ °C; $V_{RD} = V_{RRM}, V_{DD} = V_{DRM}$ | max. 85                | mA    |
| $t_{gd}$         | $T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs       | 1                      | μs    |
| $t_{gr}$         | $V_D = 0,67 * V_{DRM}$                                  | 2                      | μs    |
| $(di/dt)_{cr}$   | $T_{vj} = 130$ °C                                       | max. 250               | A/μs  |
| $(dv/dt)_{cr}$   | $T_{vj} = 130$ °C                                       | max. 1000              | V/μs  |
| $t_q$            | $T_{vj} = 130$ °C                                       | 50 ... 150             | μs    |
| $I_H$            | $T_{vj} = 25$ °C; typ. / max.                           | 150 / 500              | mA    |
| $I_L$            | $T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.             | 300 / 2000             | mA    |
| $V_{GT}$         | $T_{vj} = 25$ °C; d.c.                                  | min. 3                 | V     |
| $I_{GT}$         | $T_{vj} = 25$ °C; d.c.                                  | min. 200               | mA    |
| $V_{GD}$         | $T_{vj} = 130$ °C; d.c.                                 | max. 0,25              | V     |
| $I_{GD}$         | $T_{vj} = 130$ °C; d.c.                                 | max. 10                | mA    |
| $R_{th(j-c)}$    | cont.; per thyristor / per module                       | 0,11 / 0,055           | K/W   |
| $R_{th(j-c)}$    | sin. 180; per thyristor / per module                    | 0,116 / 0,058          | K/W   |
| $R_{th(j-c)}$    | rec. 120; per thyristor / per module                    | 0,13 / 0,065           | K/W   |
| $R_{th(c-s)}$    | per thyristor / per module                              | 0,04 / 0,02            | K/W   |
| $T_{vj}$         |                                                         | - 40 ... + 130         | °C    |
| $T_{stg}$        |                                                         | - 40 ... + 130         | °C    |
| $V_{isol}$       | a. c. 50 Hz; r.m.s.; 1 s / 1 min.                       | 3600 / 3000            | V~    |
| $M_s$            | to heatsink                                             | 5 ± 15 % <sup>1)</sup> | Nm    |
| $M_t$            | to terminals                                            | 9 ± 15 %               | Nm    |
| $a$              |                                                         | 5 * 9,81               | m/s²  |
| $m$              | approx.                                                 | 600                    | g     |
| Case             | SKKT<br>SKKH                                            | A 73b<br>A 76b         |       |



**SKKT**



**SKKH**

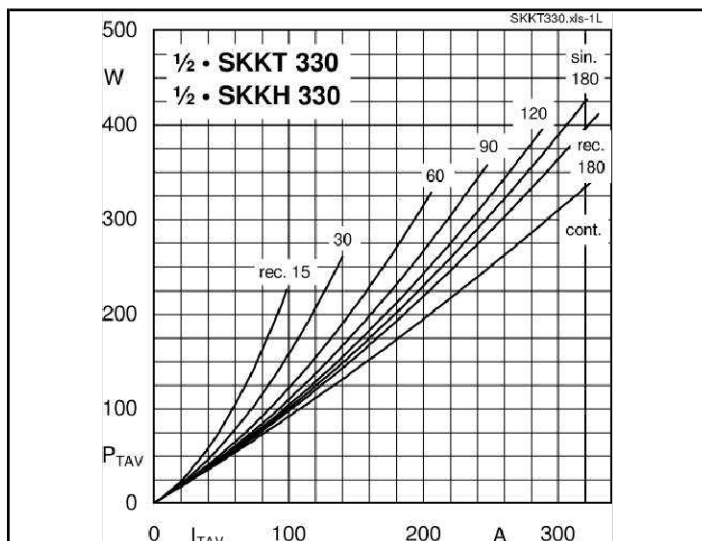


Fig. 1L Power dissipation per thyristor vs. on-state current

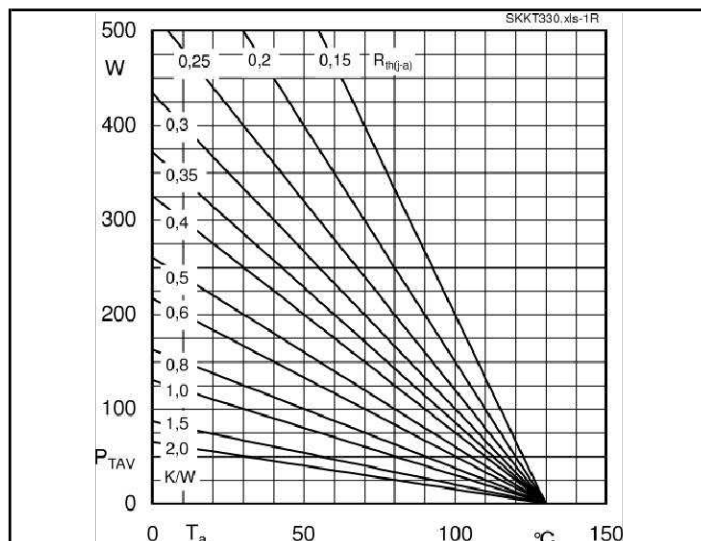


Fig. 1R Power dissipation per thyristor vs. ambient temp.

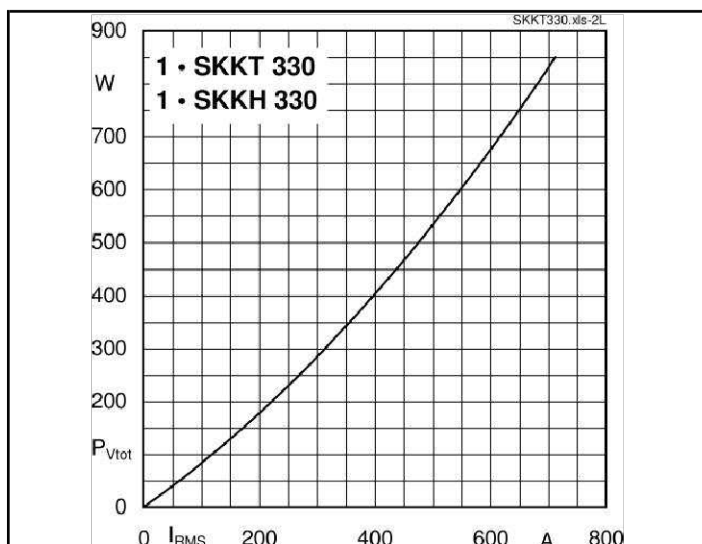


Fig. 2L Power dissipation per module vs. rms current

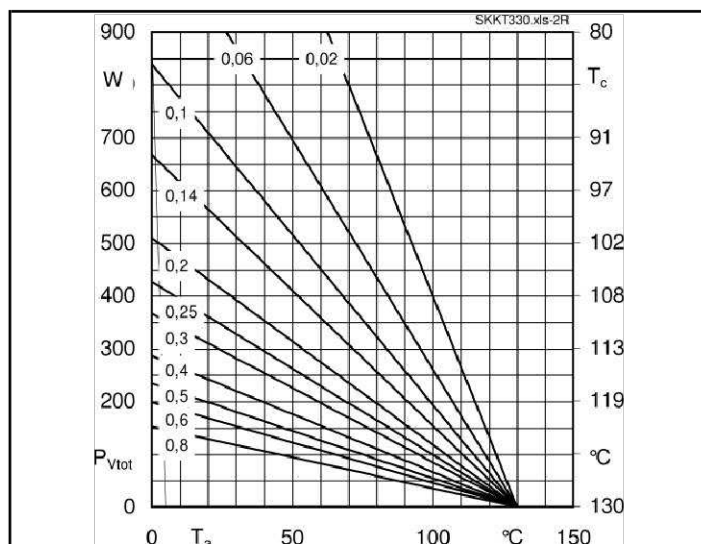


Fig. 2R Power dissipation per module vs. case temp.

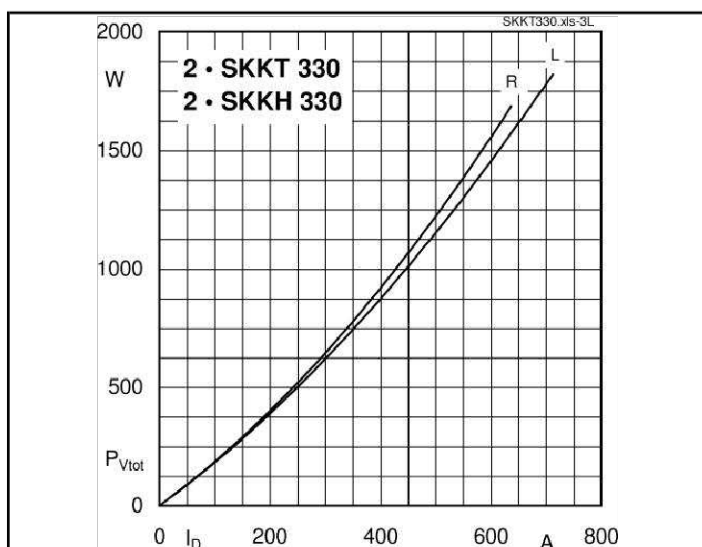


Fig. 3L Power dissipation of two modules vs. direct current

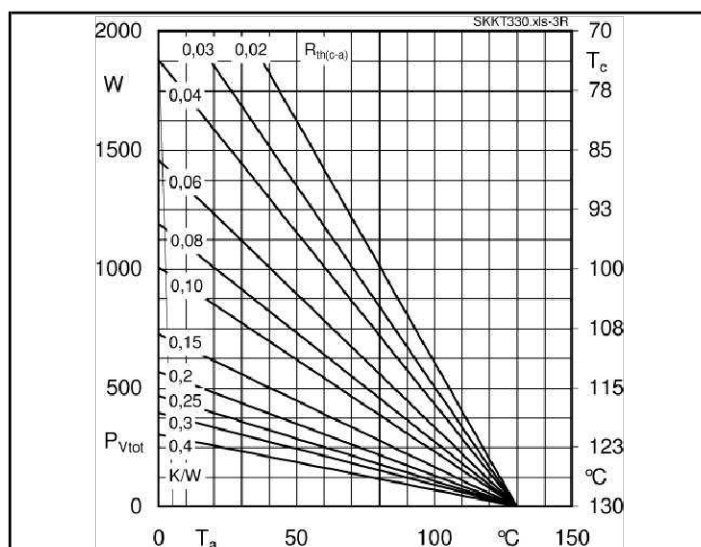


Fig. 3R Power dissipation of two modules vs. case temp.

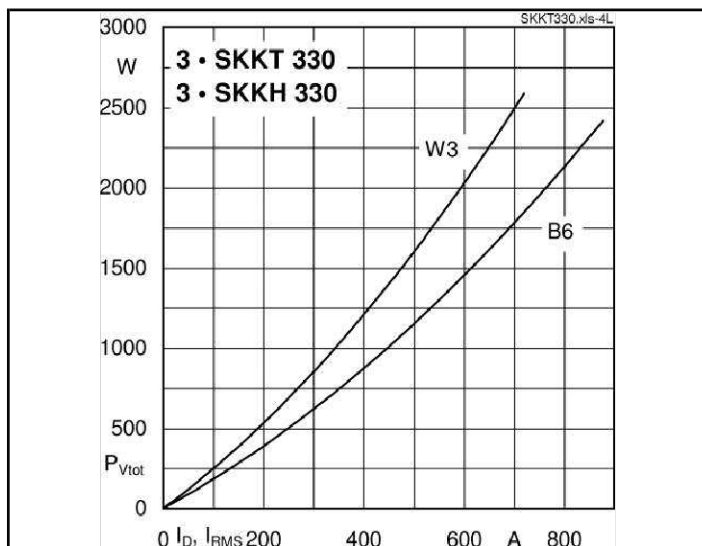


Fig. 4L Power dissipation of three modules vs. direct and rms current

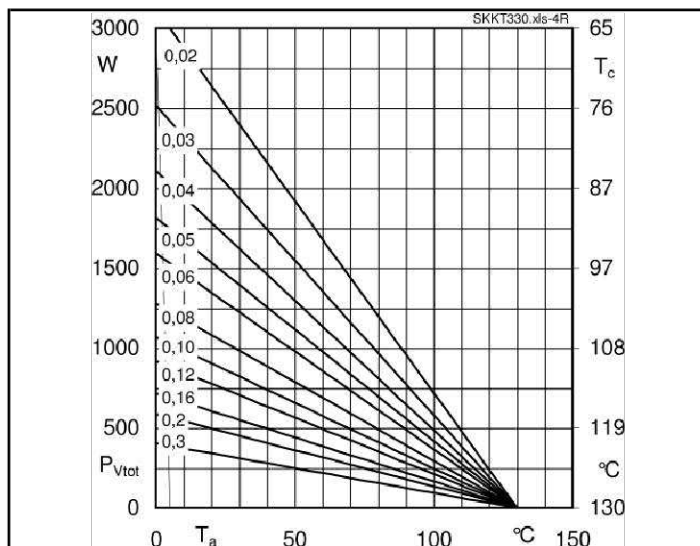


Fig. 4R Power dissipation of three modules vs. case temp.

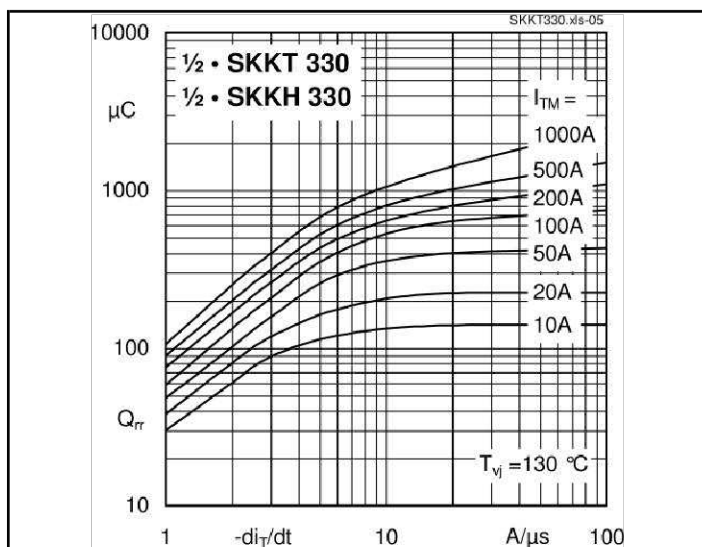


Fig. 5 Recovered charge vs. current decrease

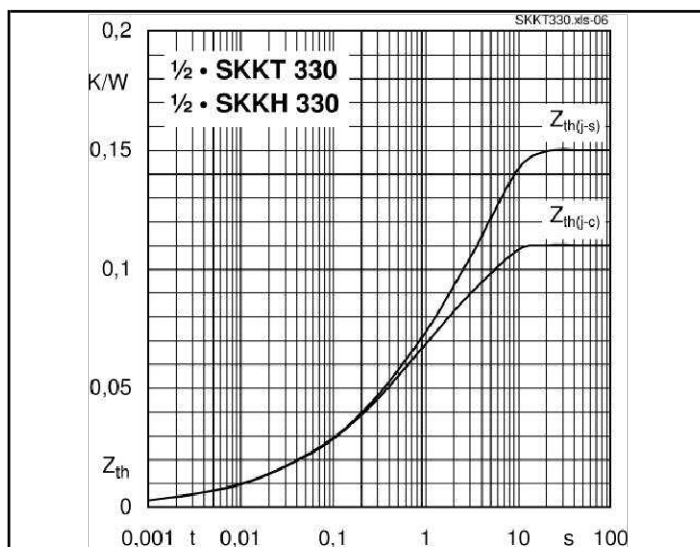


Fig. 6 Transient thermal impedance vs. time

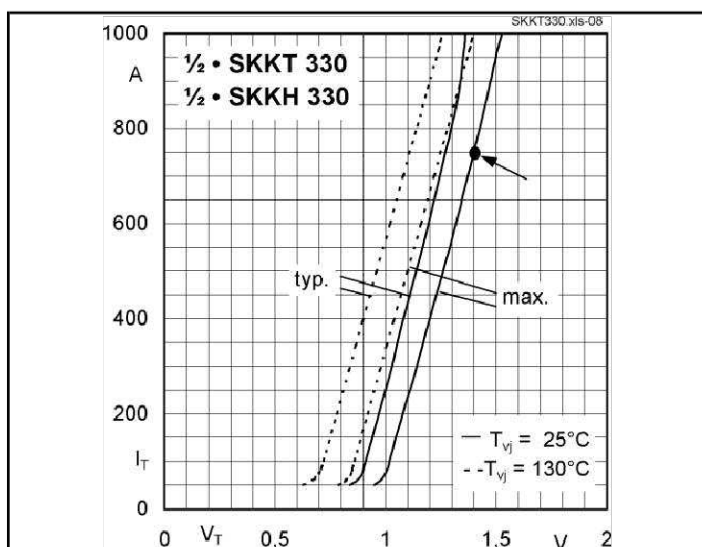


Fig. 7 On-state characteristics

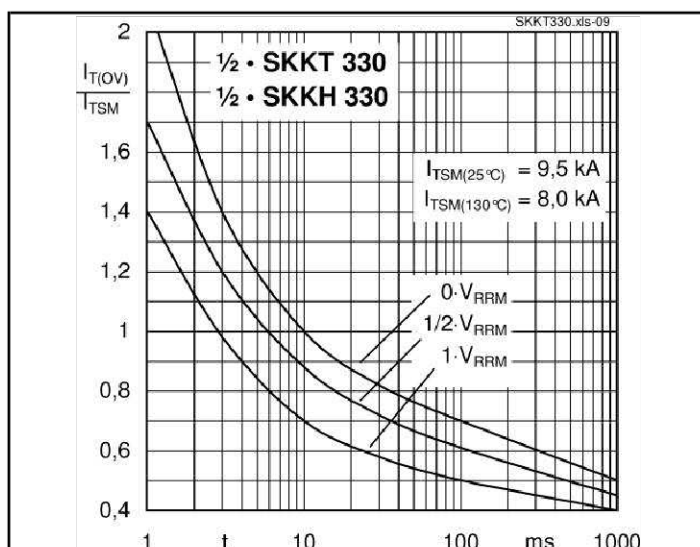
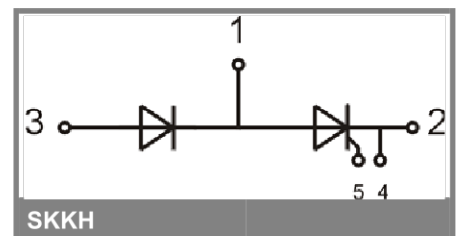
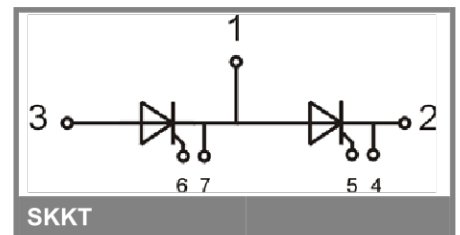
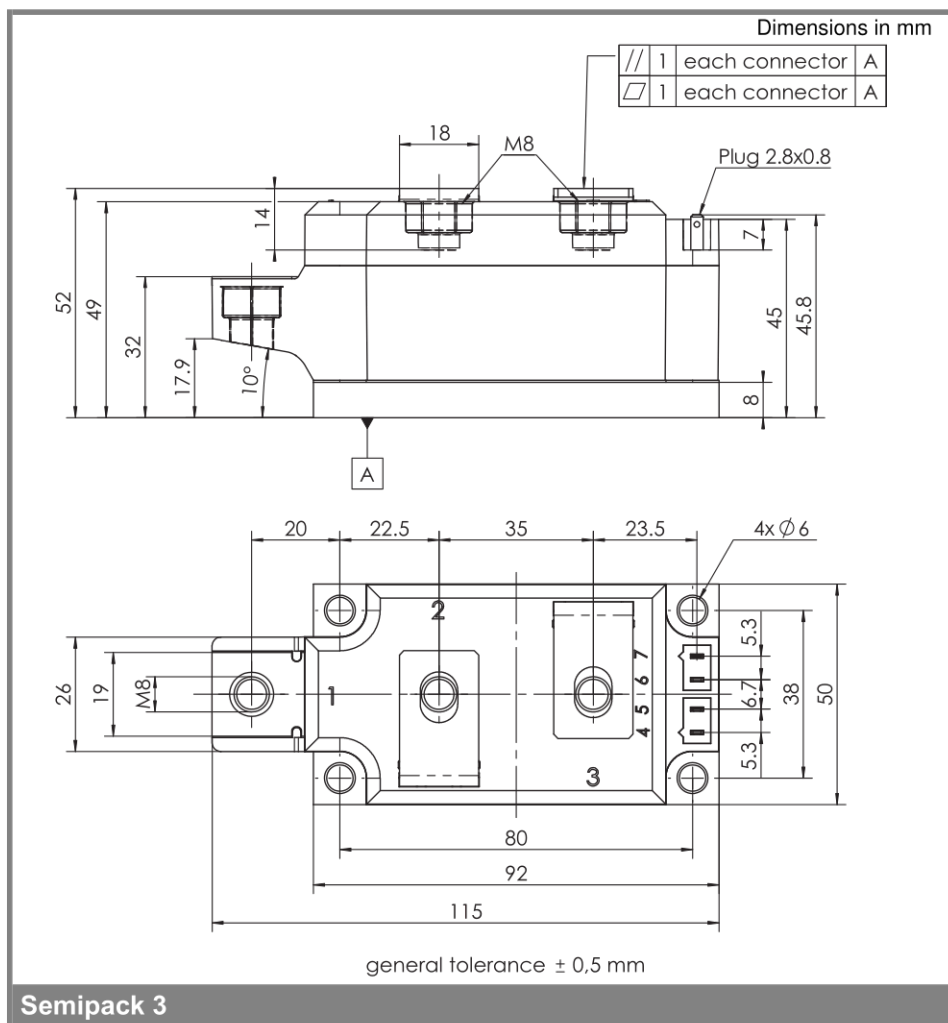
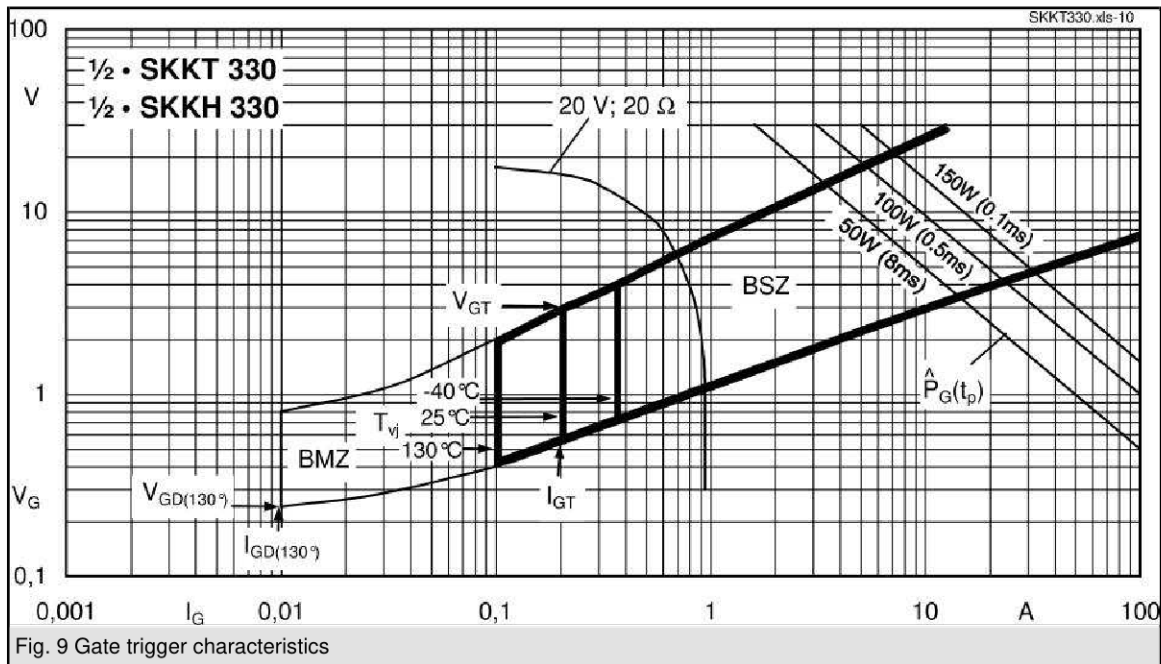


Fig. 8 Surge overload current vs. time



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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